

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property  
Organization  
International Bureau

(43) International Publication Date  
28 October 2021 (28.10.2021)



(10) International Publication Number  
**WO 2021/216449 A1**

(51) International Patent Classification:  
*H01J 37/32* (2006.01)

(21) International Application Number:  
PCT/US2021/027967

(22) International Filing Date:  
19 April 2021 (19.04.2021)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
16/856,878 23 April 2020 (23.04.2020) US

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW,

(54) Title: FACEPLATE WITH EDGE FLOW CONTROL

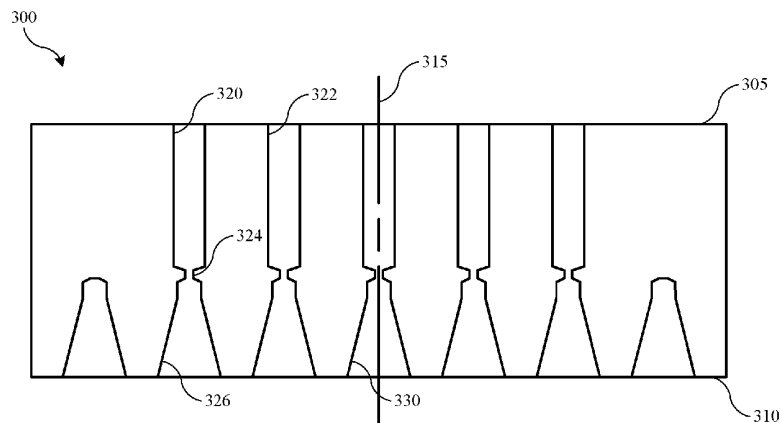


FIG. 3

(57) Abstract: Exemplary semiconductor processing chambers may include a gasbox. The chambers may include a substrate support. The chambers may include a blocker plate positioned between the gasbox and the substrate support. The blocker plate may define a plurality of apertures through the plate. The chambers may include a faceplate positioned between the blocker plate and substrate support. The faceplate may be characterized by a first surface facing the blocker plate and a second surface opposite the first surface. The second surface of the faceplate and the substrate support may at least partially define a processing region within the semiconductor processing chamber. The faceplate may be characterized by a central axis, and the faceplate may define a plurality of apertures through the faceplate. The faceplate may define a plurality of recesses extending about and radially outward of the plurality of apertures. Each recess of the plurality of recesses may extend from the second surface of the faceplate to a depth less than a thickness of the faceplate.

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SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN,  
TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

**(84) Designated States** (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

**Published:**

— with international search report (Art. 21(3))